**Product data sheet** 

## 1. General description

P-channel enhancement mode Field-Effect Transistor (FET) in a leadless ultra small DFN1006-3 (SOT883) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

#### 2. Features and benefits

- Trench MOSFET technology
- Low threshold voltage
- Very fast switching
- ElectroStatic Discharge (ESD) protection > 1.8 kV HBM
- Leadless ultra small SMD plastic package: 1.0 × 0.6 × 0.48 mm

## 3. Applications

- Relay driver
- High-speed line driver
- High-side loadswitch
- Switching circuits

### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> = 25 °C		-	-	-20	V
V <sub>GS</sub>	gate-source voltage			-8	-	8	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = -4.5 V; T <sub>amb</sub> = 25 °C; t ≤ 5 s	[1]	-	-	-1.4	Α
Static characteristics							
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS} = -4.5 \text{ V}; I_D = -0.3 \text{ A}; T_j = 25 \text{ °C}$		-	330	450	mΩ

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm<sup>2</sup>.



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# 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	1 🔲	D I
2	S	source	23	
3	D	drain	Transparent top view  DFN1006-3 (SOT883)	G S 017aaa259

# 6. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
PMZ350UPE	DFN1006-3	DFN1006-3: leadless ultra small plastic package; 3 solder lands	SOT883		

# 7. Marking

Table 4. Marking codes

Type number	Marking code
PMZ350UPE	ZP

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# 8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit	
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	-20	V	
V <sub>GS</sub>	gate-source voltage			-8	8	V	
I <sub>D</sub>	drain current	$V_{GS} = -4.5 \text{ V}; T_{amb} = 25 \text{ °C}; t \le 5 \text{ s}$	[1]	-	-1.4	Α	
		V <sub>GS</sub> = -4.5 V; T <sub>amb</sub> = 25 °C	[1]	-	-1	Α	
		V <sub>GS</sub> = -4.5 V; T <sub>amb</sub> = 100 °C	[1]	-	-0.7	Α	
I <sub>DM</sub>	peak drain current	$T_{amb}$ = 25 °C; single pulse; $t_p \le 10 \mu s$		-	-2.8	Α	
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C	<u>[2]</u>	-	360	mW	
			[1]	-	715	mW	
		T <sub>sp</sub> = 25 °C		-	3125	mW	
Tj	junction temperature			-55	150	°C	
T <sub>amb</sub>	ambient temperature			-55	150	°C	
T <sub>stg</sub>	storage temperature			-65	150	°C	
Source-drain of	diode		'	'		,	
I <sub>S</sub>	source current	T <sub>amb</sub> = 25 °C	[1]	-	-0.8	Α	
ESD maximum	ESD maximum rating						
V <sub>ESD</sub>	electrostatic discharge voltage	НВМ	[3]	-	1800	V	

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm<sup>2</sup>.

<sup>[2]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

<sup>[3]</sup> Measured between all pins.

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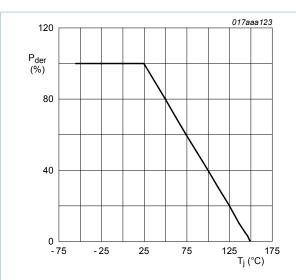


Fig. 1. Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

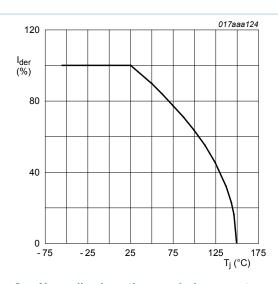


Fig. 2. Normalized continuous drain current as a function of junction temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100 \%$$

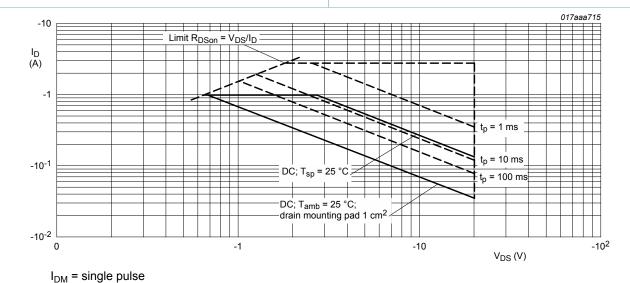


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drainsource voltage

### 9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R <sub>th(j-a)</sub>	thermal resistance	in free air	[1]	-	304	350	K/W
	from junction to ambient		[2]	-	150	175	K/W
			[3]	-	90	103	K/W

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point		-	35	40	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm<sup>2</sup>.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm $^2$ , t  $\leq$  5 s.

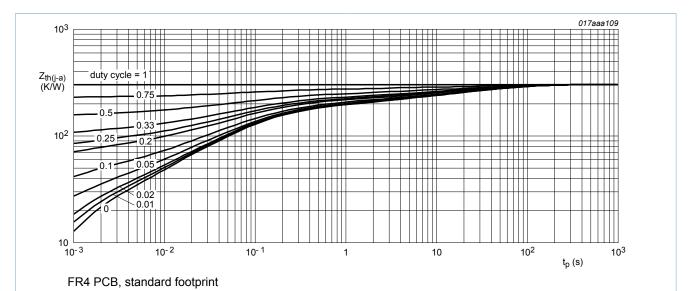
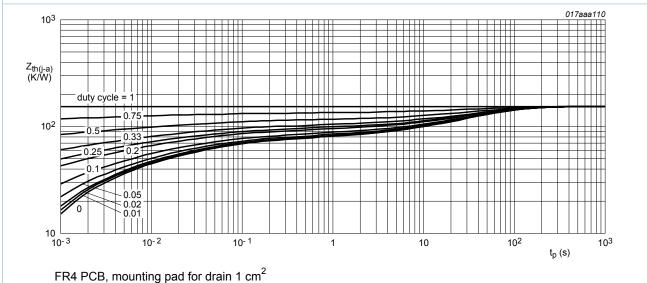


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



1 14 1 CB, mounting pad for drain 1 cm

Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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## 10. Characteristics

#### Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static char	acteristics					
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = -250 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^{\circ}C$	-20	-	-	V
$V_{GSth}$	gate-source threshold voltage	$I_D = -250 \ \mu A; \ V_{DS} = V_{GS}; \ T_j = 25 \ ^{\circ}C$	-0.45	-0.7	-0.95	V
I <sub>DSS</sub> drain leakage curren	drain leakage current	V <sub>DS</sub> = -20 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-1	μΑ
		V <sub>DS</sub> = -20 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 150 °C	-	-	-10	μΑ
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = -8 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-10	μA
		V <sub>GS</sub> = 8 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	10	μA
R <sub>DSon</sub>	drain-source on-state	V <sub>GS</sub> = -4.5 V; I <sub>D</sub> = -0.3 A; T <sub>j</sub> = 25 °C	-	330	450	mΩ
resistan	resistance	V <sub>GS</sub> = -4.5 V; I <sub>D</sub> = -0.3 A; T <sub>j</sub> = 150 °C	-	478	645	mΩ
		V <sub>GS</sub> = -2.5 V; I <sub>D</sub> = -0.2 A; T <sub>j</sub> = 25 °C	-	420	645	mΩ
		V <sub>GS</sub> = -1.8 V; I <sub>D</sub> = -0.1 A; T <sub>j</sub> = 25 °C	-	520	940	mΩ
9 <sub>fs</sub>	forward transconductance	$V_{DS}$ = -10 V; $I_{D}$ = -0.3 A; $T_{j}$ = 25 °C	-	1.4	-	S
Dynamic cl	naracteristics					
Q <sub>G(tot)</sub>	total gate charge	$V_{DS}$ = -10 V; $I_{D}$ = -0.3 A; $V_{GS}$ = -4.5 V;	-	1.3	1.9	nC
Q <sub>GS</sub>	gate-source charge	T <sub>j</sub> = 25 °C	-	0.2	-	nC
$Q_{GD}$	gate-drain charge		-	0.25	-	nC
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = -10 V; f = 1 MHz; V <sub>GS</sub> = 0 V;	-	127	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C	-	34	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	25	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = -10 V; $I_{D}$ = -0.3 A; $V_{GS}$ = -4.5 V;	-	4	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)}$ = 6 $\Omega$ ; $T_j$ = 25 °C	-	5	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	26	-	ns
t <sub>f</sub>	fall time		-	9	-	ns
Source-dra	in diode		I	1	1	
$V_{SD}$	source-drain voltage	I <sub>S</sub> = -0.1 A; V <sub>GS</sub> = 0 V; T <sub>i</sub> = 25 °C	-	-0.7	-1.2	V

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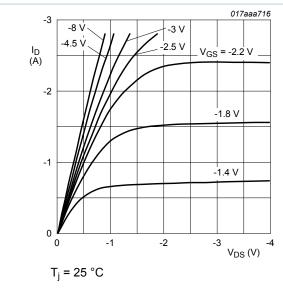
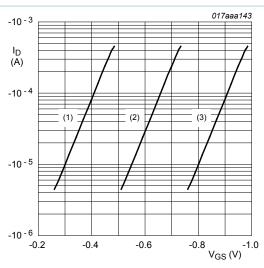


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values



$$T_i$$
 = 25 °C;  $V_{DS}$  = -3  $V$ 

- (1) minimum values
- (2) typical values
- (3) maximum values

Fig. 7. Sub-threshold drain current as a function of gate-source voltage

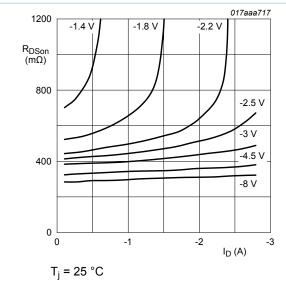


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

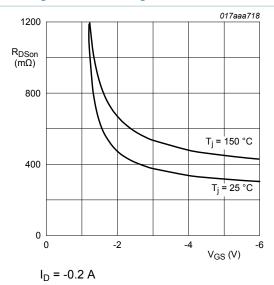


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

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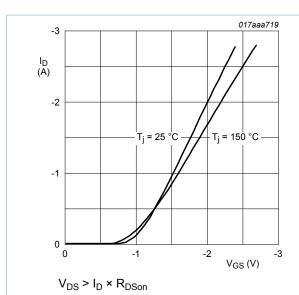


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

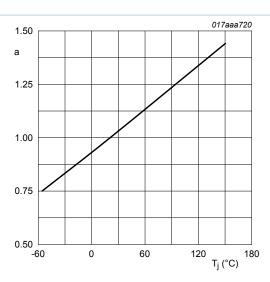


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

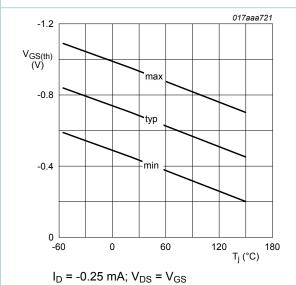
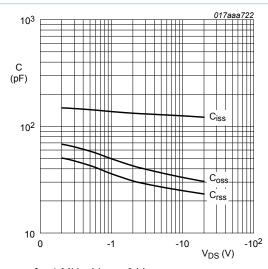


Fig. 12. Gate-source threshold voltage as a function of junction temperature



 $f = 1 MHz; V_{GS} = 0 V$ 

Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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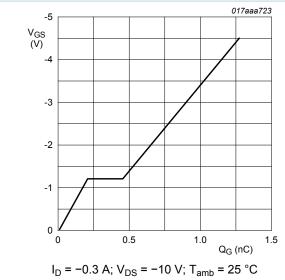


Fig. 14. Gate-source voltage as a function of gate charge; typical values

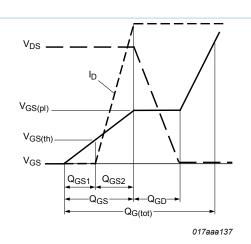


Fig. 15. Gate charge waveform definitions

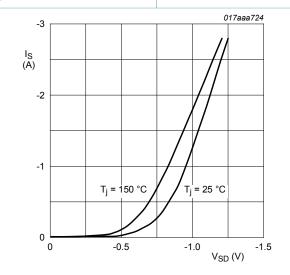
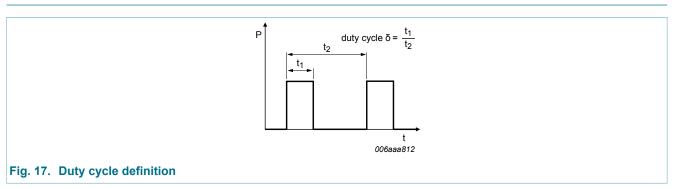


Fig. 16. Source current as a function of source-drain voltage; typical values

## 11. Test information

 $V_{GS} = 0 V$ 



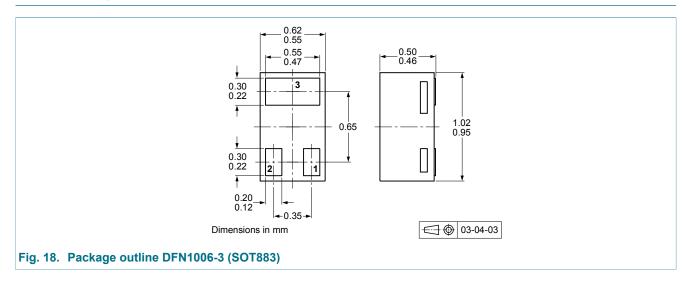
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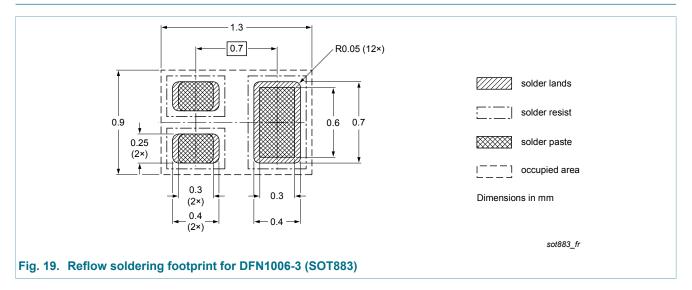
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## 12. Package outline



# 13. Soldering



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# 14. Revision history

### Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMZ350UPE v.1	20140514	Product data sheet	-	-

#### 20 V, P-channel Trench MOSFET

## 15. Legal information

#### 15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
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Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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